10-F1127PA025SC-L167E09
datasheet

***flow*7PACK 1** **1200 V / 25 A**

Topology features

- Brake+Inverter
- Kelvin emitter
- Open Emitter configuration
- Temperature sensor

Component features

- Easy paralleling
- Low turn-off losses
- Low collector emitter saturation voltage
- Positive temperature coefficient
- Short tail current

Housing features

- Base isolation: Al_2O_3
- Convex shaped substrate for superior thermal contact
- Thermo-mechanical push-and-pull force relief
- Solder pin

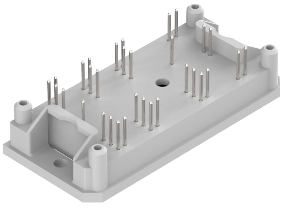
Target applications

- Motor Drives
- Power Generation

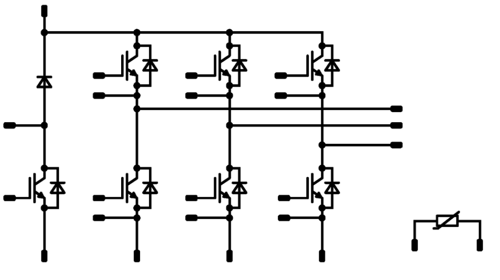
Types

- 10-F1127PA025SC-L167E09

flow 1 17 mm housing



Schematic



Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Inverter Switch					
Collector-emitter voltage	V_{CES}			1200	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$	T_s = 80 °C	34	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}		75	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	99	W
Gate-emitter voltage	V_{GES}			±20	V
Short circuit ratings	t_{SC}	V_{GE} = 15 V, V_{CC} = 800 V	T_j = 150 °C	10	µs
Maximum junction temperature	T_{jmax}			175	°C
Inverter Diode					
Peak repetitive reverse voltage	V_{RRM}			1200	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	30	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		50	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	60	W
Maximum junction temperature	T_{jmax}			175	°C
Brake Switch					
Collector-emitter voltage	V_{CES}			1200	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$	T_s = 80 °C	34	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}		75	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	99	W
Gate-emitter voltage	V_{GES}			±20	V
Short circuit ratings	t_{SC}	V_{GE} = 15 V, V_{CC} = 800 V	T_j = 150 °C	10	µs
Maximum junction temperature	T_{jmax}			175	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Brake Diode					
Peak repetitive reverse voltage	V_{RRM}			1200	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	20	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		20	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	46	W
Maximum junction temperature	T_{jmax}			175	°C
Brake Sw. Protection Diode					
Peak repetitive reverse voltage	V_{RRM}			1200	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	10	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		6	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	25	W
Maximum junction temperature	T_{jmax}			150	°C
Module Properties					
Thermal Properties					
Storage temperature	T_{stg}			-40…+125	°C
Operation temperature under switching condition	T_{jop}			-40…+(T_{jmax} - 25)	°C
Isolation Properties					
Isolation voltage	V_{isol}	DC Test Voltage*	t_p = 2 s	6000	V
Isolation voltage	V_{isol}	AC Voltage	t_p = 1 min	2500	V
Creepage distance				>12,7	mm
Clearance				>12,7	mm
Comparative Tracking Index	CTI			≥ 200	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Inverter Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,00085	25	5,3	5,8	6,3	V
Collector-emitter saturation voltage	V_{CEsat}		15		25	25 125 150	1,58	1,96 2,23 2,27	2,07(1)	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			2,4	µA
Gate-emitter leakage current	I_{GES}		20	0		25			120	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	f = 1 Mhz	0	25		25		1450		pF
Reverse transfer capacitance	C_{res}	f = 1 Mhz	0	25		25		50		pF
Gate charge	Q_g		±15		0	25		200		nC
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,96		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 16 Ω R_{goff} = 16 Ω	±15	600	25	25 150		66,4 67,4		ns
Rise time	t_r	R_{gon} = 16 Ω R_{goff} = 16 Ω	±15	600	25	25 150		42,4 43,2		ns
Turn-off delay time	$t_{d(off)}$	R_{gon} = 16 Ω R_{goff} = 16 Ω	±15	600	25	25 150		196,4 264,2		ns
Fall time	t_f	R_{gon} = 16 Ω R_{goff} = 16 Ω	±15	600	25	25 150		70,81 138,28		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=2,22 µC Q_{rFWD}=4,5 µC	±15	600	25	25 150		2,13 3,15		mWs
Turn-off energy (per pulse)	E_{off}		±15	600	25	25 150		1,47 2,48		mWs

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	Unit
Inverter Diode										
Static										
Forward voltage	V_F				25	25 125 150	1,35	1,84 1,85 1,83	2,05(1)	V
Reverse leakage current	I_R	V_r = 1200 V				25			5,2	µA
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,59		K/W
Dynamic										
Peak recovery current	I_{RRM}	d*i*/d*t*=565 A/µs d*i*/d*t*=465 A/µs	±15	600	25	25 150		12,8 17,44		A
Reverse recovery time	t_{rr}					25 150		318,14 523,9		ns
Recovered charge	Q_r					25 150		2,22 4,5		µC
Reverse recovered energy	E_{rec}					25 150		0,859 1,78		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 150		115,12 91,7		A/µs

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	Unit
Brake Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,00085	25	5,3	5,8	6,3	V
Collector-emitter saturation voltage	V_{CEsat}		15		25	25 125 150	1,58	1,96 2,23 2,27	2,07(1)	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			2,4	µA
Gate-emitter leakage current	I_{GES}		20	0		25			120	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	f = 1 Mhz	0	25		25		1450		pF
Reverse transfer capacitance	C_{res}							50		pF
Gate charge	Q_g		±15		0	25		200		nC
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,96		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 32 Ω R_{goff} = 32 Ω	±15	600	25	25 125 150		123,6 123,2 123,8		ns
Rise time	t_r					25 125 150		44 46,2 46,4		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		232,4 289,4 305,2		ns
Fall time	t_f					25 125 150		66,42 130,5 150,88		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=1,42 µC Q_{rFWD}=2,58 µC Q_{rFWD}=2,85 µC				25 125 150		2 2,49 2,62		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		1,52 2,37 2,66		mWs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Brake Diode										
Static										
Forward voltage	V_F				10	25 150	1,35	1,77 1,69	2,05[1]	V
Reverse leakage current	I_R	V_r = 1200 V				25			2,7	µA
Thermal										
Thermal resistance junction to sink [2]	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						2,07		K/W
Dynamic										
Peak recovery current	I_{RRM}	d*i*/d*t*=422 A/µs d*i*/d*t*=355 A/µs d*i*/d*t*=386 A/µs	±15	600	25	25 125 150		8,94 11,15 11,53		A
Reverse recovery time	t_{rr}					25 125 150		349,17 542,26 576,34		ns
Recovered charge	Q_r					25 125 150		1,42 2,58 2,85		µC
Reverse recovered energy	E_{rec}					25 125 150		0,554 1,07 1,19		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		25,52 22,82 22,6		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Brake Sw. Protection Diode										
Static										
Forward voltage	V_F				3	25 150	1,23	1,65 1,52	1,97 (1)	V
Reverse leakage current	I_R	V_r = 1200 V				25			27	µA
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						2,8		K/W
Thermistor										
Static										
Rated resistance	R					25		22		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	R_{100} = 1484 Ω				100	-5		5	%
Power dissipation	P					25		130		mW
Power dissipation constant	d					25		1,5		mW/K
B-value	$B_{(25/50)}$	Tol. ±1 %						3962		K
B-value	$B_{(25/100)}$	Tol. ±1 %						4000		K
Vincotech Thermistor Reference									I	

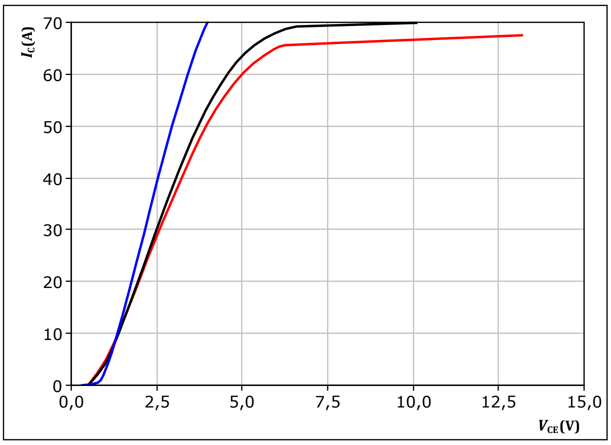
(1) Value at chip level
(2) Only valid with pre-applied Vincotech thermal interface material.

Inverter Switch Characteristics

figure 1. **IGBT**

Typical output characteristics

I_C = f(V_{CE})

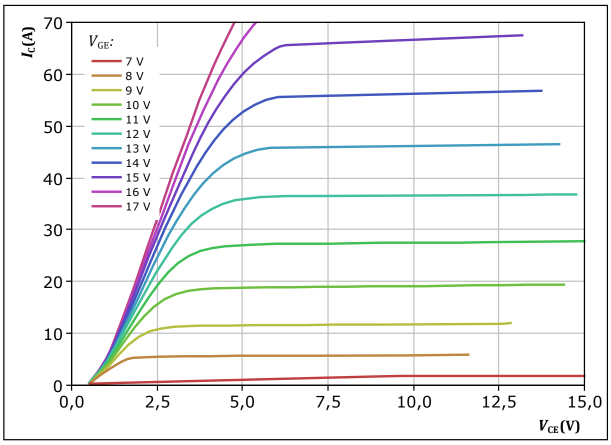


t_p =	250	µs		25 °C
V_{GE} =	15	V	T_j:	125 °C
				150 °C

figure 2. **IGBT**

Typical output characteristics

I_C = f(V_{CE})



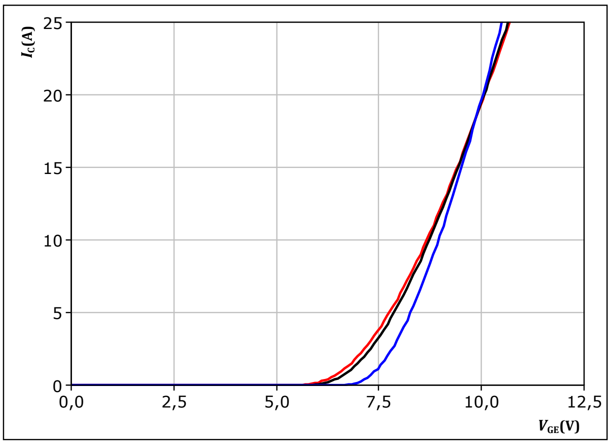
t_p =	250	µs
T_j =	150	°C

V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. **IGBT**

Typical transfer characteristics

I_C = f(V_{GE})

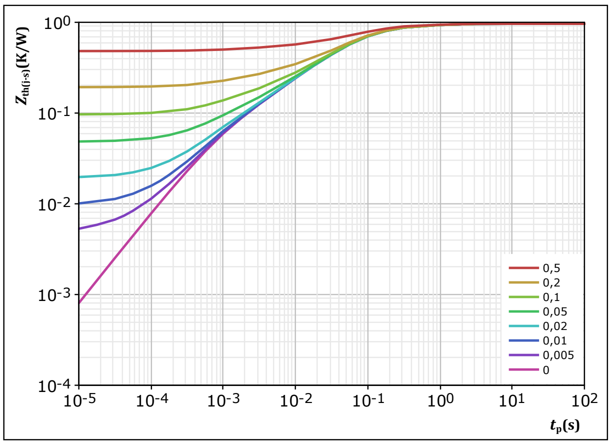


t_p =	250	µs		25 °C
V_{CE} =	10	V	T_j:	125 °C
				150 °C

figure 4. **IGBT**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D =	t_p / T	
$R_{th(j-s)}$ =	0,964	K/W

IGBT thermal model values

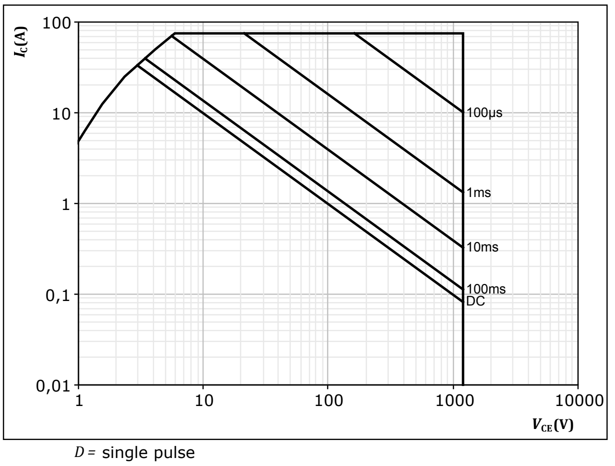
R (K/W)	τ (s)
9,34E-02	8,35E-01
3,42E-01	1,19E-01
3,61E-01	4,14E-02
1,15E-01	7,70E-03
5,33E-02	9,80E-04

Inverter Switch Characteristics

figure 5.	IGBT

Safe operating area

I_C = f(V_{CE})



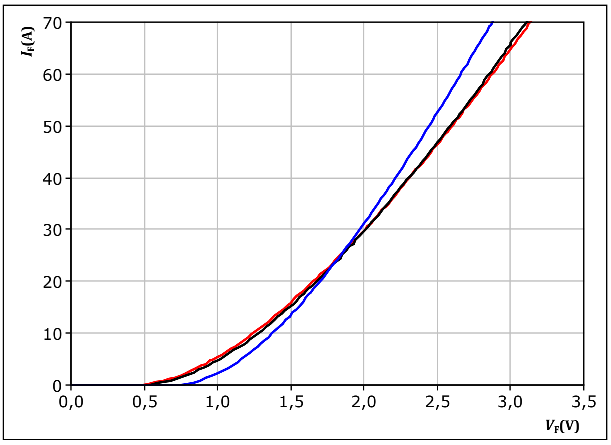
D =	single pulse	
T_s =	80	°C
V_{GE} =	15	V
T_j =	T_{jmax}	

Inverter Diode Characteristics

figure 6. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



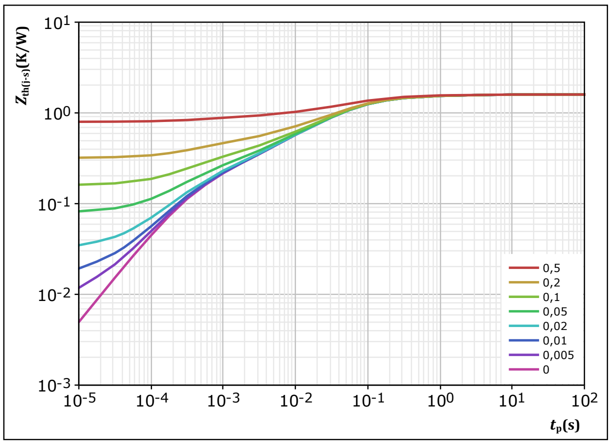
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 7. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 1,594 K/W

FWD thermal model values

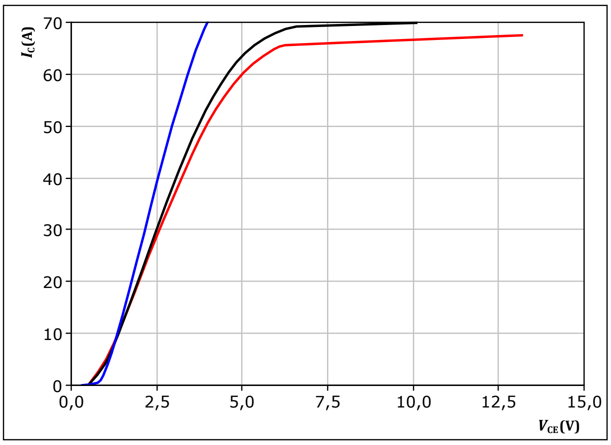
R (K/W)	τ (s)
7,80E-02	2,61E+00
3,11E-01	2,04E-01
6,92E-01	4,64E-02
2,79E-01	8,74E-03
9,99E-02	1,79E-03
1,35E-01	3,39E-04

Brake Switch Characteristics

figure 8. **IGBT**

Typical output characteristics

I_C = f(V_{CE})

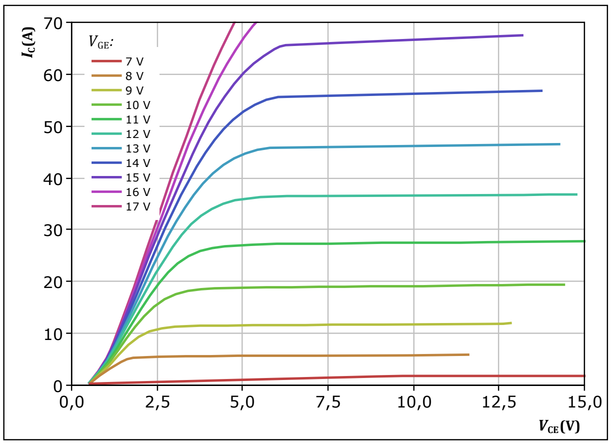


t_p =	250	µs		25 °C
V_{GE} =	15	V	T_j:	125 °C
				150 °C

figure 9. **IGBT**

Typical output characteristics

I_C = f(V_{CE})



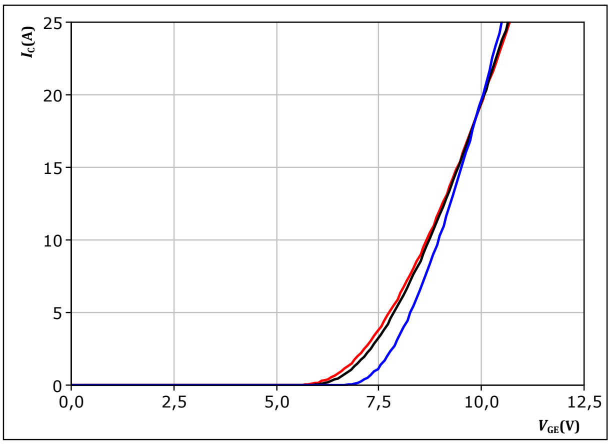
t_p =	250	µs
T_j =	150	°C

V_{GE} from 7 V to 17 V in steps of 1 V

figure 10. **IGBT**

Typical transfer characteristics

I_C = f(V_{GE})

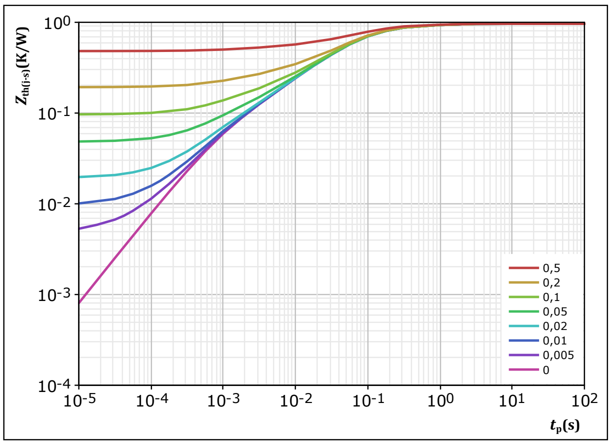


t_p =	250	µs		25 °C
V_{CE} =	10	V	T_j:	125 °C
				150 °C

figure 11. **IGBT**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D =	t_p / T	
$R_{th(j-s)}$ =	0,964	K/W

IGBT thermal model values

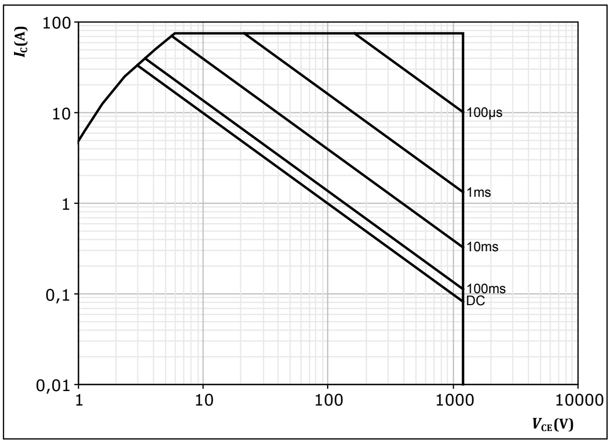
R (K/W)	τ (s)
9,34E-02	8,35E-01
3,42E-01	1,19E-01
3,61E-01	4,14E-02
1,15E-01	7,70E-03
5,33E-02	9,80E-04

Brake Switch Characteristics

figure 12.	IGBT

Safe operating area

I_C = f(V_{CE})



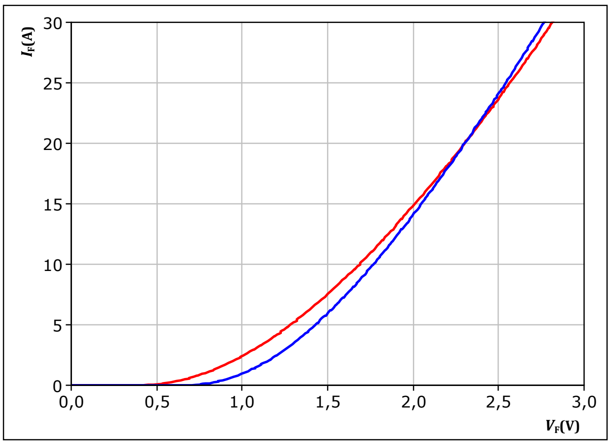
D =	single pulse	
T_s =	80	°C
V_{GE} =	15	V
T_j =	T_{jmax}	

Brake Diode Characteristics

figure 13. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



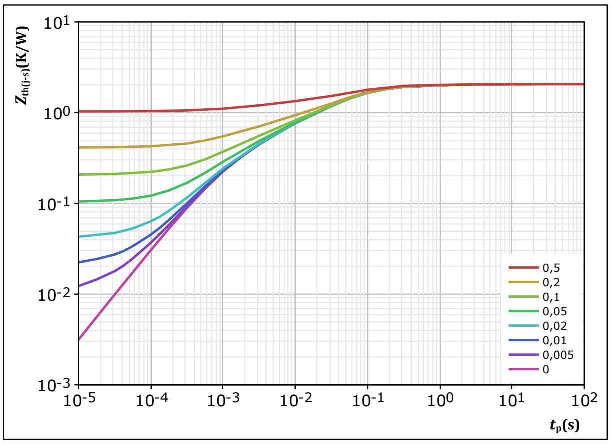
t_p = 250 µs

T_j: 25 °C, 150 °C

figure 14. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 2,066 K/W

FWD thermal model values

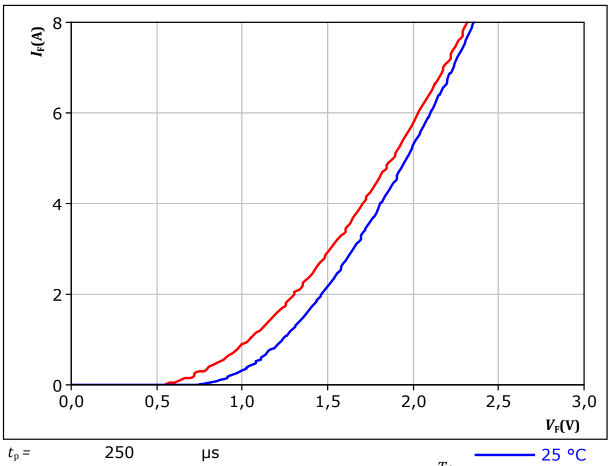
R (K/W)	τ (s)
5,09E-02	4,26E+00
1,55E-01	5,03E-01
7,75E-01	7,89E-02
5,33E-01	2,68E-02
3,54E-01	5,03E-03
1,97E-01	9,09E-04

Brake Sw. Protection Diode Characteristics

figure 15. FWD

Typical forward characteristics

$I_F = f(V_F)$



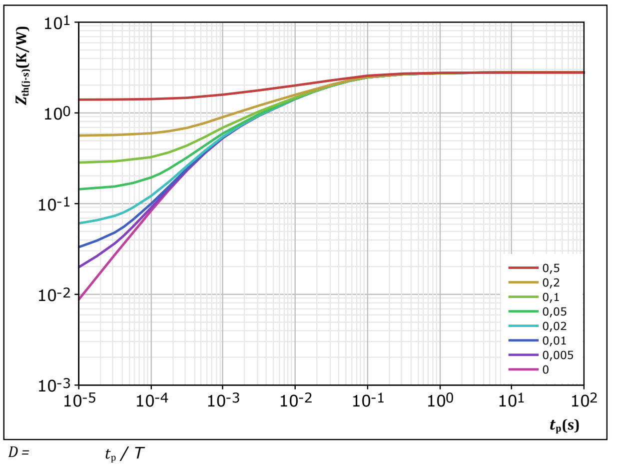
t_p = 250 µs

T_j: 25 °C, 150 °C

figure 16. FWD

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 2,796 K/W

FWD thermal model values

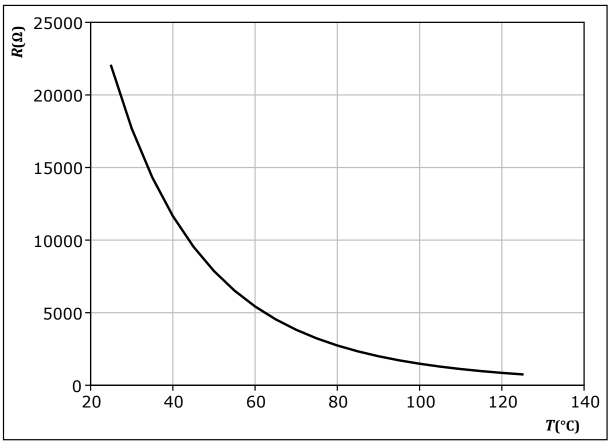
R (K/W)	τ (s)
7,82E-02	2,45E+00
1,95E-01	2,65E-01
9,84E-01	4,77E-02
6,58E-01	1,23E-02
5,09E-01	2,70E-03
3,71E-01	5,98E-04

Thermistor Characteristics

figure 17.	Thermistor

Typical NTC characteristic as function of temperature

R_T = f(T)

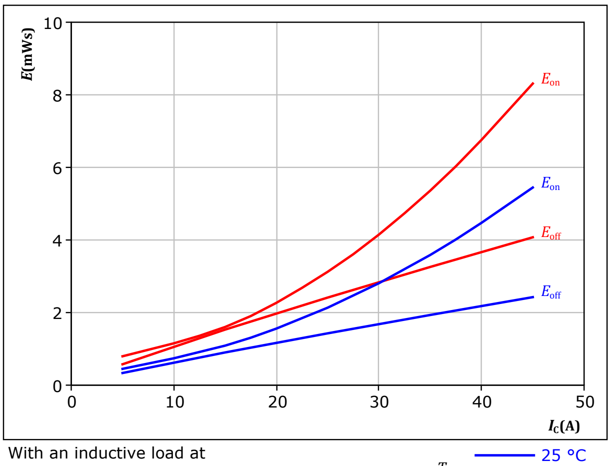


Inverter Switching Characteristics

figure 18. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



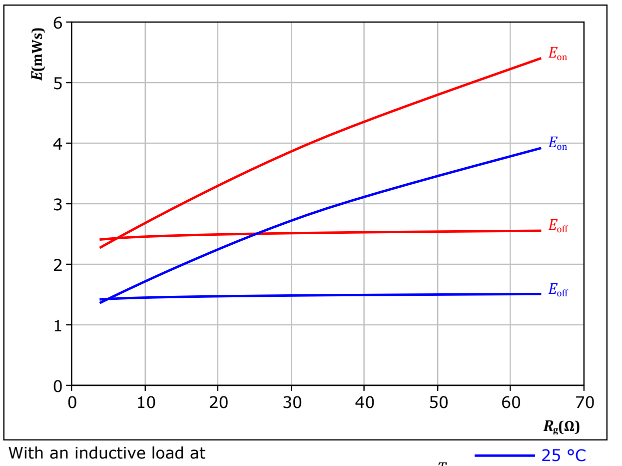
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		150 °C
R_{gon} =	16	Ω		
R_{goff} =	16	Ω		

figure 19. **IGBT**

Typical switching energy losses as a function of IGBT turn on gate resistor

$E = f(R_g)$



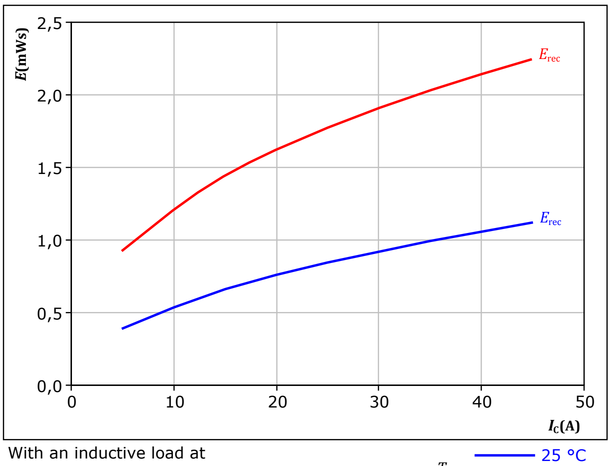
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		150 °C
I_C =	25	A		

figure 20. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



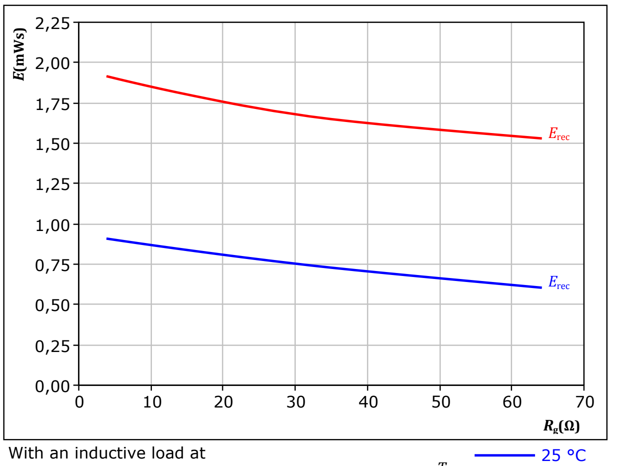
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		150 °C
R_{gon} =	16	Ω		

figure 21. **FWD**

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

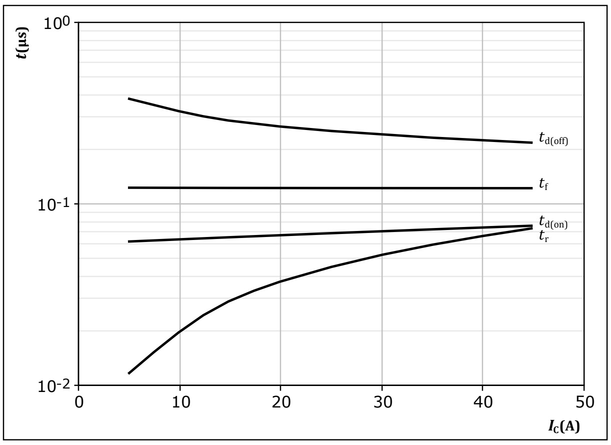
V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		150 °C
I_C =	25	A		

Inverter Switching Characteristics

figure 22. **IGBT**

Typical switching times as a function of collector current

t = f(I_C)



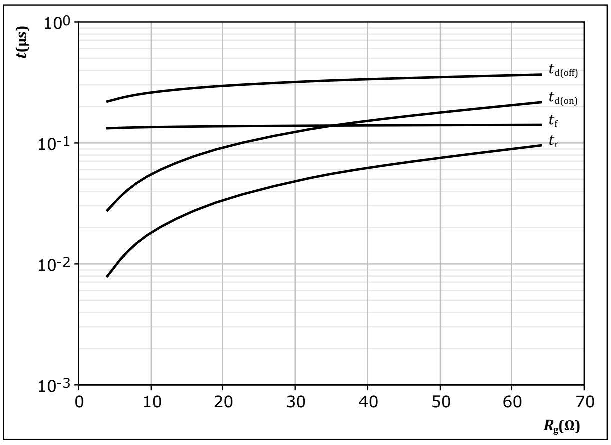
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	16	Ω
R_{goff} =	16	Ω

figure 23. **IGBT**

Typical switching times as a function of IGBT turn on gate resistor

t = f(R_g)



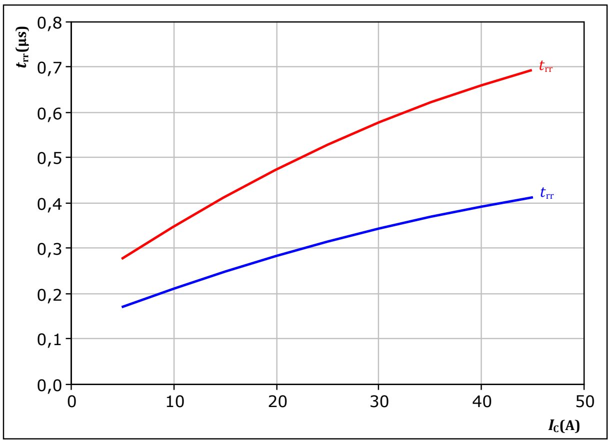
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	25	A

figure 24. **FWD**

Typical reverse recovery time as a function of collector current

t_{rr} = f(I_C)



With an inductive load at

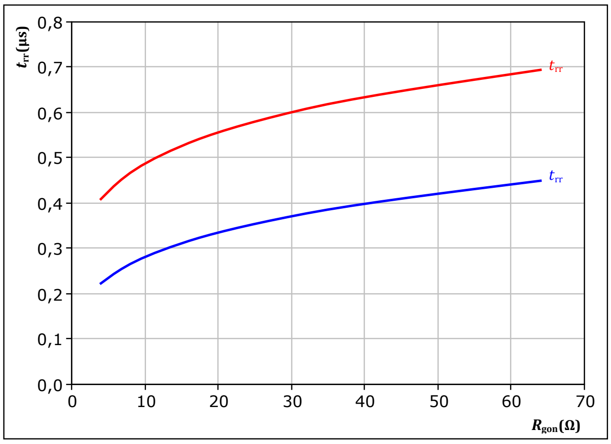
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	16	Ω

T_j: 25 °C, 150 °C

figure 25. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



With an inductive load at

V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	25	A

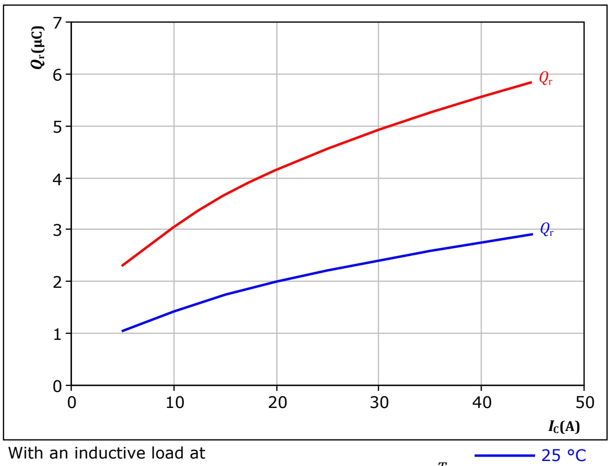
T_j: 25 °C, 150 °C

Inverter Switching Characteristics

figure 26. **FWD**

Typical recovered charge as a function of collector current

$Q_r = f(I_C)$



With an inductive load at

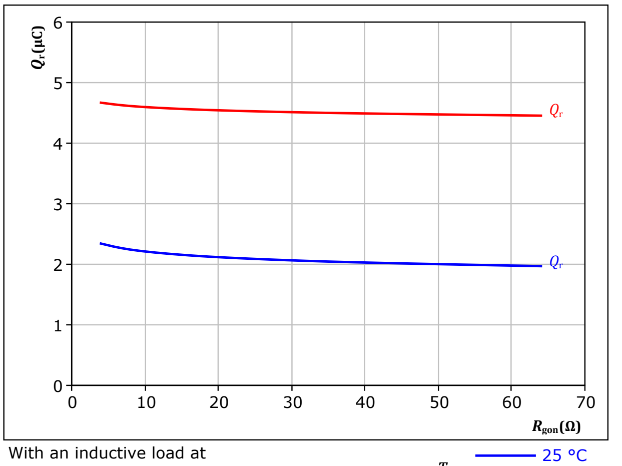
T_j: 25 °C / 150 °C

V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	16	Ω

figure 27. **FWD**

Typical recovered charge as a function of IGBT turn on gate resistor

$Q_r = f(R_{gon})$



With an inductive load at

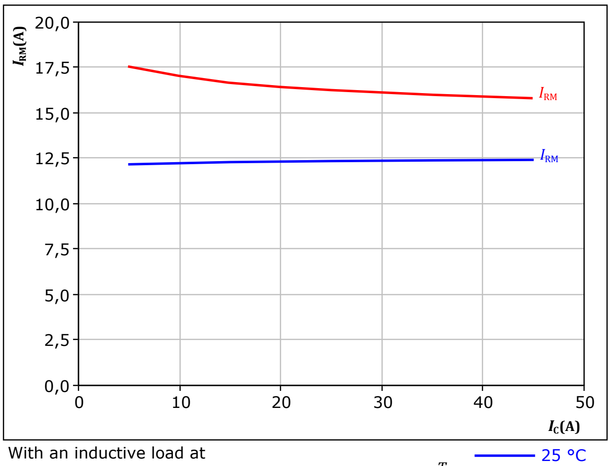
T_j: 25 °C / 150 °C

V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	25	A

figure 28. **FWD**

Typical peak reverse recovery current as a function of collector current

$I_{RM} = f(I_C)$



With an inductive load at

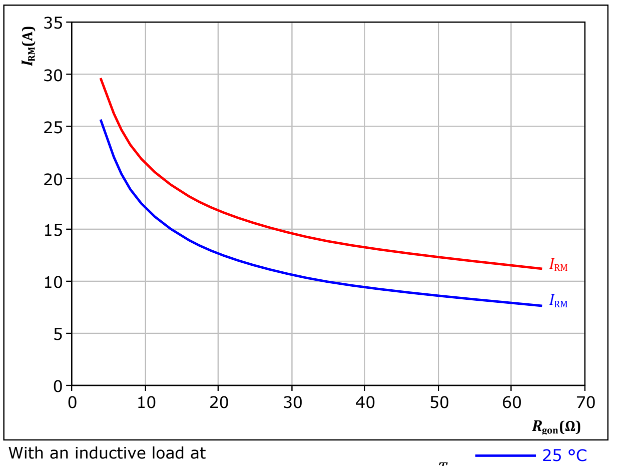
T_j: 25 °C / 150 °C

V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	16	Ω

figure 29. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

$I_{RM} = f(R_{gon})$



With an inductive load at

T_j: 25 °C / 150 °C

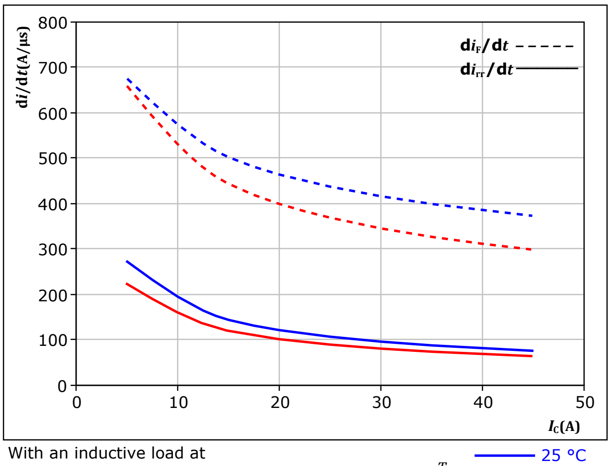
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	25	A

Inverter Switching Characteristics

figure 30. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



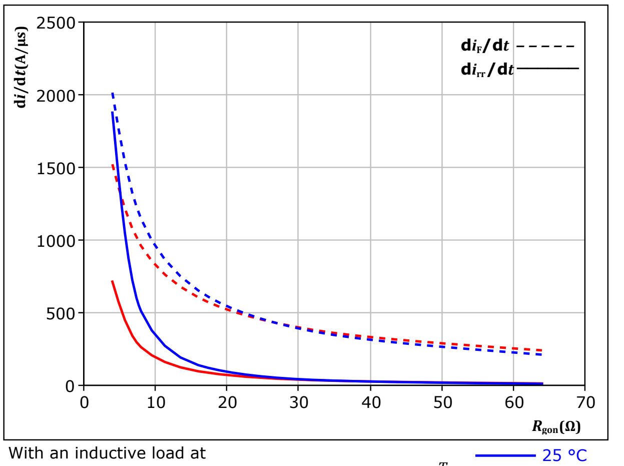
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		150 °C
R_{gon} =	16	Ω		

figure 31. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})



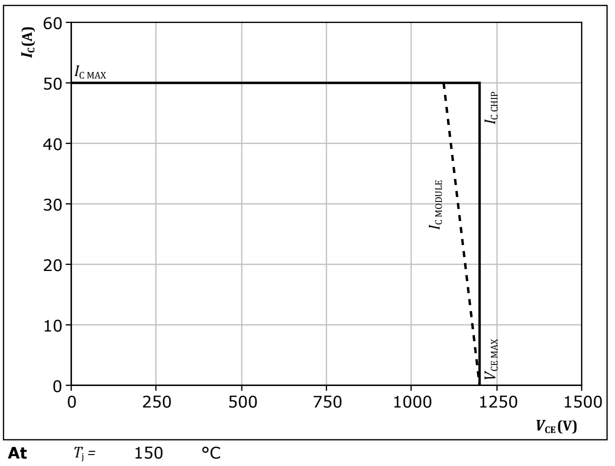
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		150 °C
I_C =	25	A		

figure 32. **IGBT**

Reverse bias safe operating area

I_C = f(V_{CE})



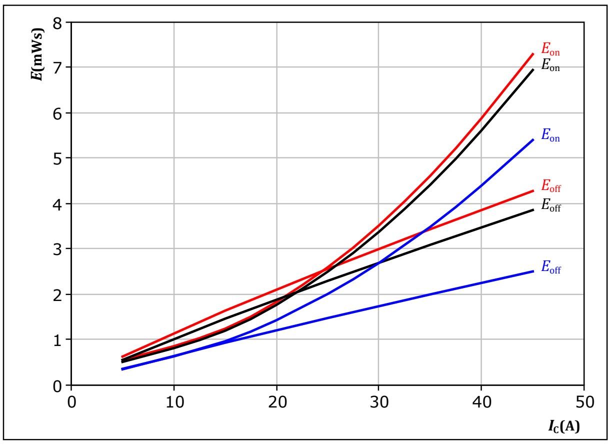
At	T_j =	150	°C
	R_{gon} =	16	Ω
	R_{goff} =	16	Ω

Brake Switching Characteristics

figure 33. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



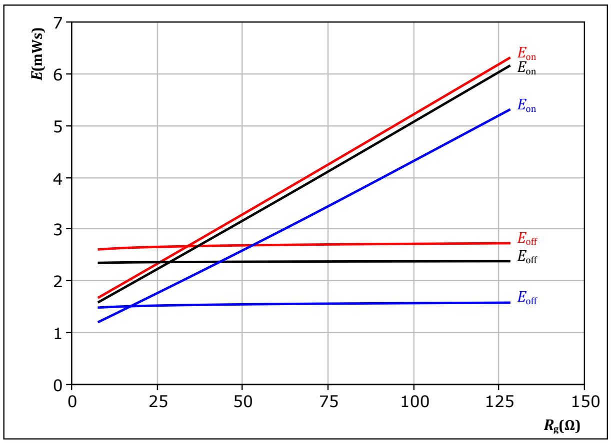
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C	
V_{GE} =	±15	V		125 °C	
R_{gon} =	32	Ω		150 °C	
R_{goff} =	32	Ω			

figure 34. **IGBT**

Typical switching energy losses as a function of IGBT turn on gate resistor

$E = f(R_g)$



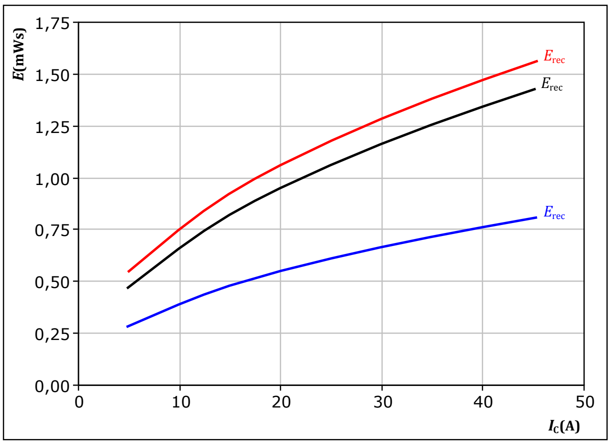
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	25	A		150 °C

figure 35. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



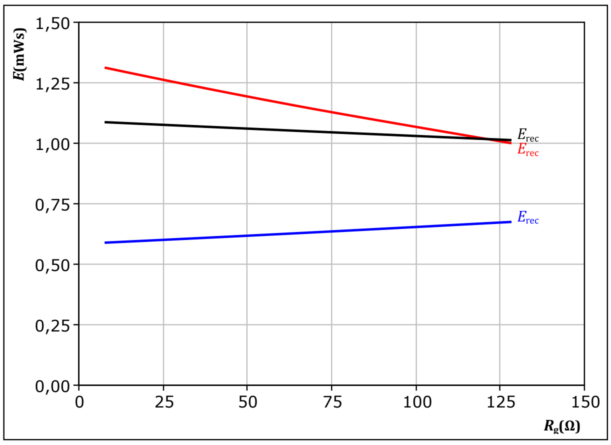
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	32	Ω		150 °C

figure 36. **FWD**

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

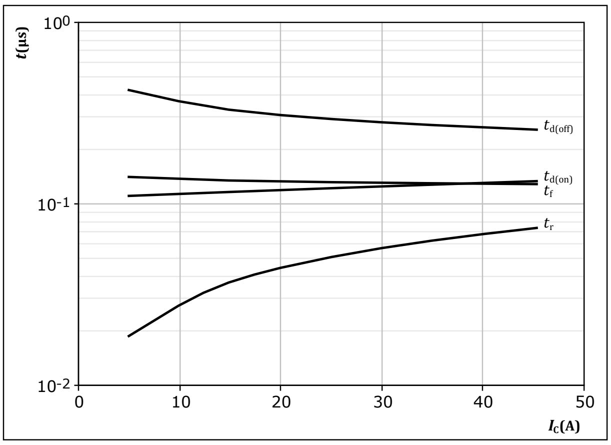
V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	25	A		150 °C

Brake Switching Characteristics

figure 37. **IGBT**

Typical switching times as a function of collector current

$t = f(I_C)$



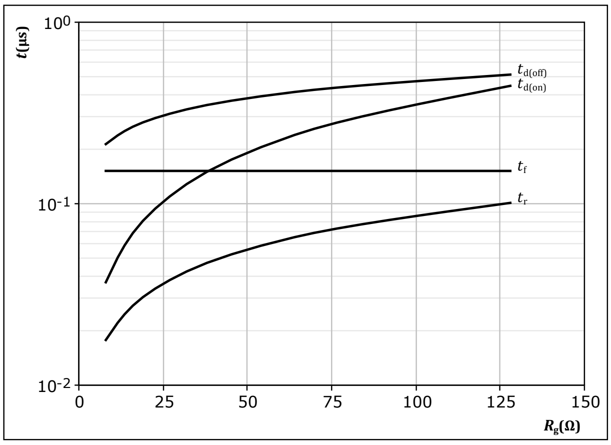
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	32	Ω
R_{goff} =	32	Ω

figure 38. **IGBT**

Typical switching times as a function of IGBT turn on gate resistor

$t = f(R_g)$



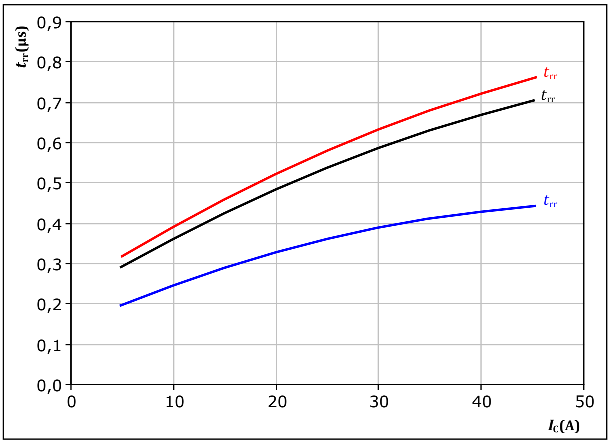
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	25	A

figure 39. **FWD**

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$



With an inductive load at

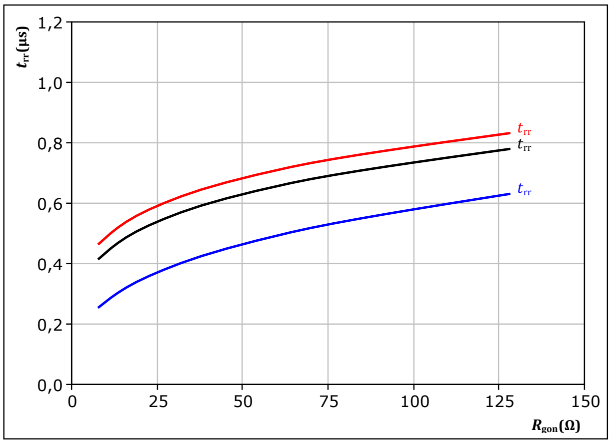
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	32	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 40. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



With an inductive load at

V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	25	A

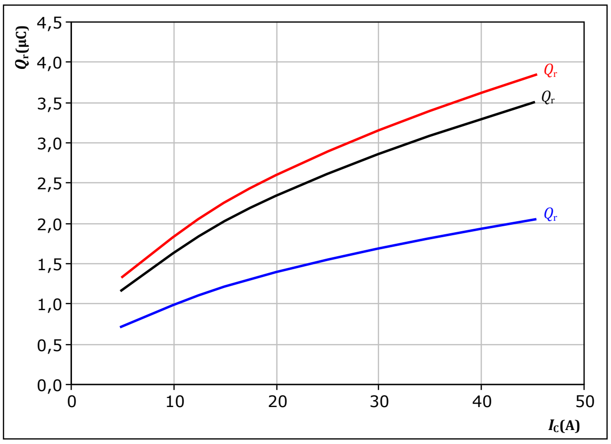
T_j: 25 °C, 125 °C, 150 °C

Brake Switching Characteristics

figure 41. **FWD**

Typical recovered charge as a function of collector current

$Q_r = f(I_C)$



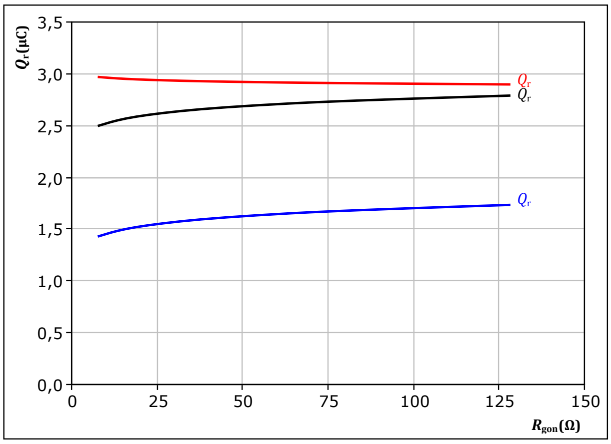
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	32	Ω		150 °C

figure 42. **FWD**

Typical recovered charge as a function of IGBT turn on gate resistor

$Q_r = f(R_{gon})$



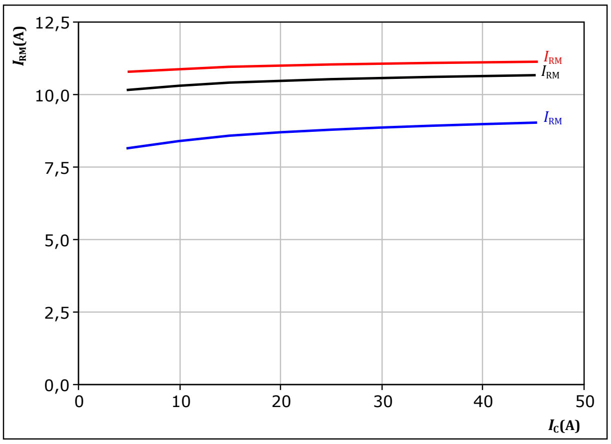
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	25	A		150 °C

figure 43. **FWD**

Typical peak reverse recovery current as a function of collector current

$I_{RM} = f(I_C)$



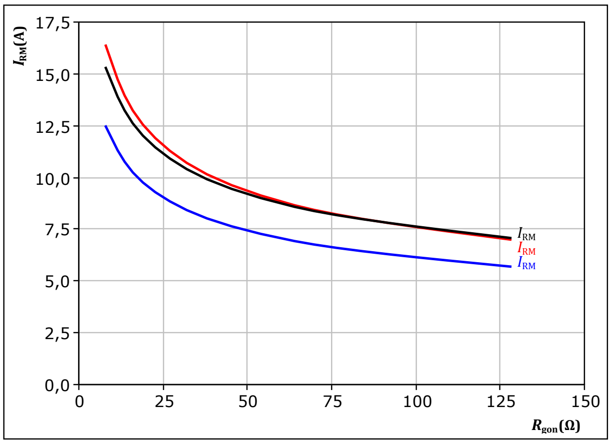
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	32	Ω		150 °C

figure 44. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

$I_{RM} = f(R_{gon})$



With an inductive load at

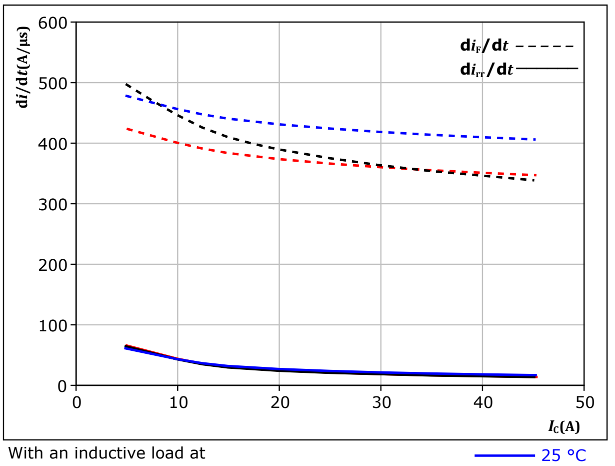
V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	25	A		150 °C

Brake Switching Characteristics

figure 45. FWD

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



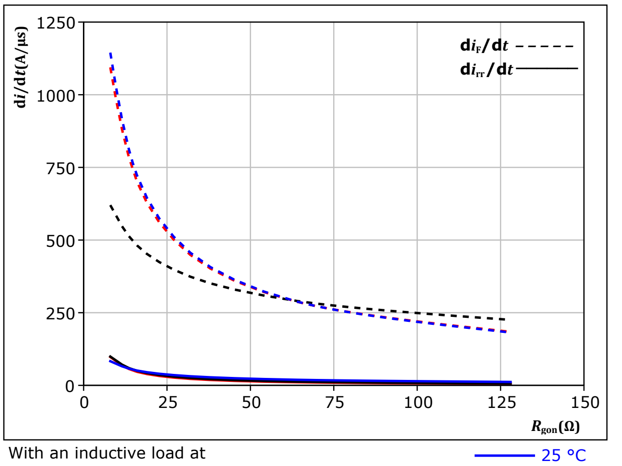
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	32	Ω		150 °C

figure 46. FWD

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})



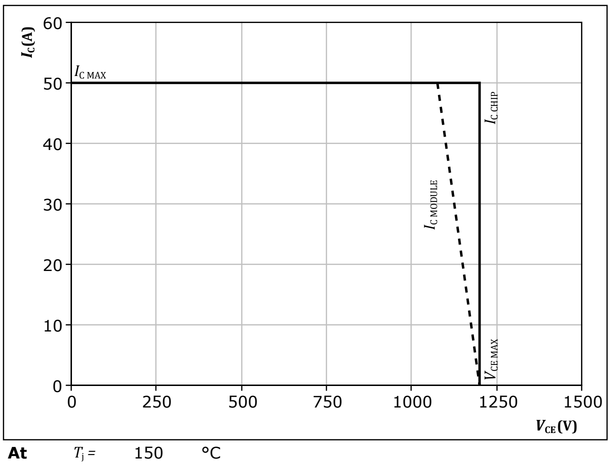
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	25	A		150 °C

figure 47. IGBT

Reverse bias safe operating area

I_C = f(V_{CE})



At	T_j =	150	°C
	R_{gon} =	32	Ω
	R_{goff} =	32	Ω

Switching Definitions

figure 48. **IGBT**

Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{tEoff} = integrating time for E_{off})

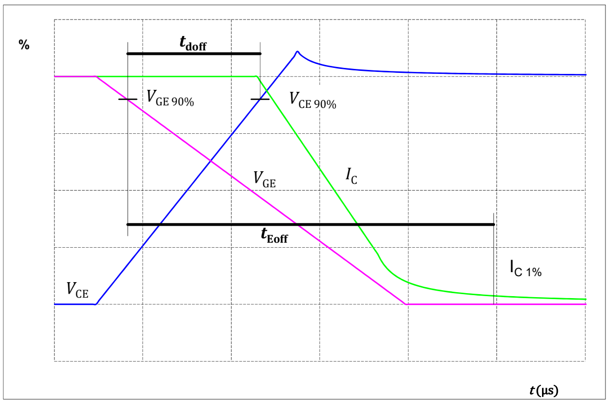


figure 49. **IGBT**

Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})

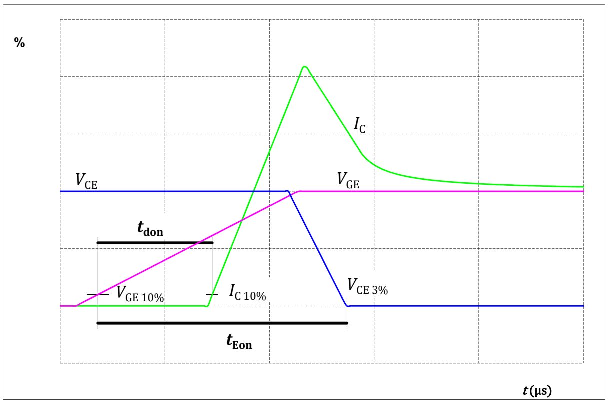


figure 50. **IGBT**

Turn-off Switching Waveforms & definition of t_f

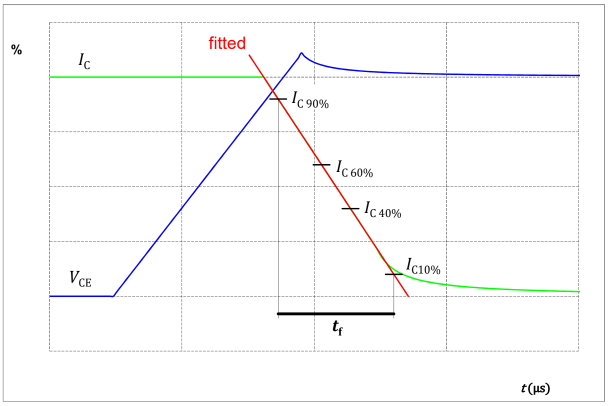
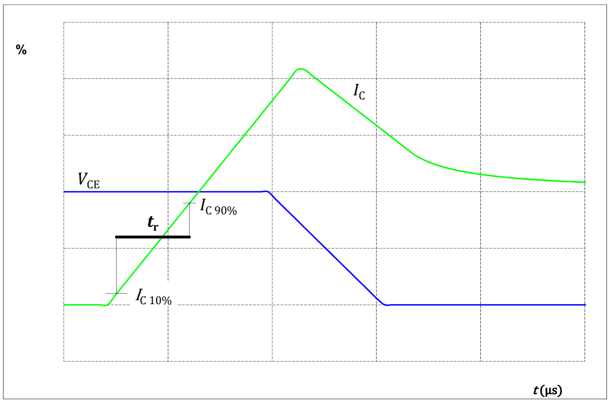


figure 51. **IGBT**

Turn-on Switching Waveforms & definition of t_r



Switching Definitions

figure 52. **FWD**

Turn-off Switching Waveforms & definition of t_{rr}

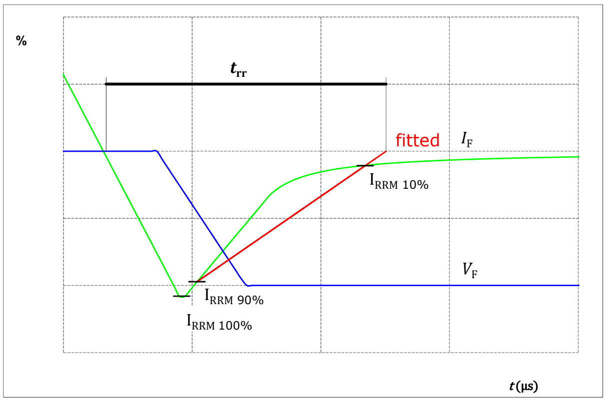
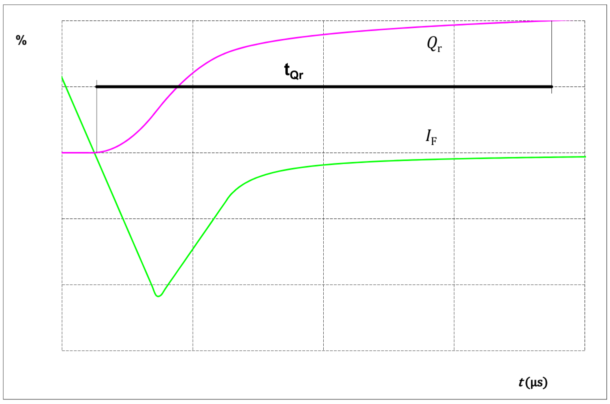


figure 53. **FWD**

Turn-on Switching Waveforms & definition of t_{Qr} **(**t_{Qr} **= integrating time for** Q_r**)**



10-F1127PA025SC-L167E09
datasheet

Ordering Code

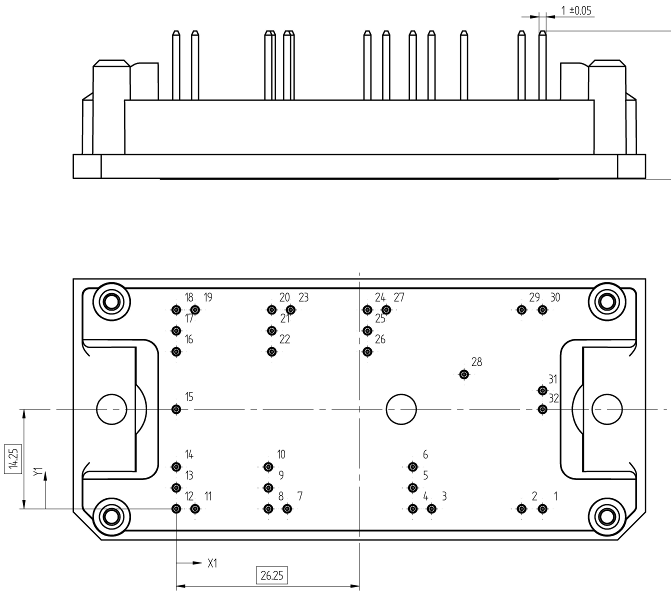
Version	Ordering Code
Without thermal paste	10-F1127PA025SC-L167E09
With thermal paste (5,2 W/mK, PTM6000HV)	10-F1127PA025SC-L167E09-/7/
With thermal paste (3,4 W/mK, PSX-P7)	10-F1127PA025SC-L167E09-/3/

Marking

	**Text**	**Name**		**Date code**	**UL & VIN**	**Lot**	**Serial**
		NN-NNNNNNNNNNNNNN-TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
	Datamatrix	**Type&Ver**	**Lot number**	**Serial**	**Date code**		
		TTTTTTTVV	LLLLL	SSSS	WWYY		

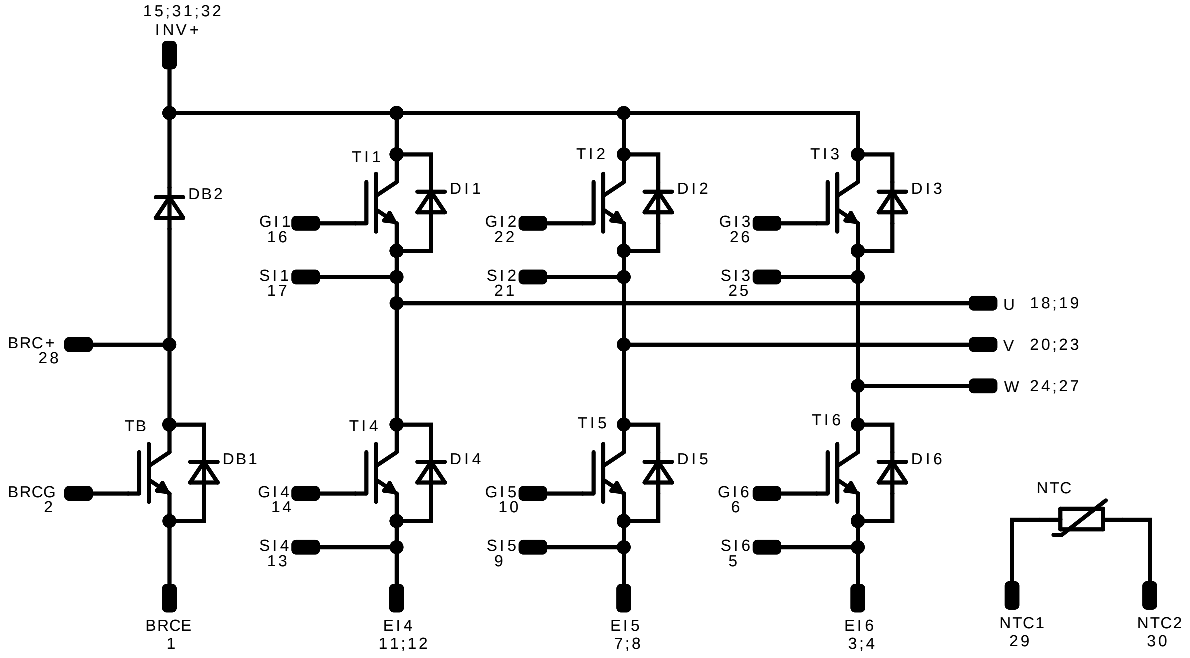
Outline

Pin table [mm]			
Pin	X	Y	Function
1	52,5	0	BRCE
2	49,5	0	BRCG
3	36,6	0	EI6
4	33,9	0	EI6
5	33,9	3	SI6
6	33,9	6	GI6
7	15,9	0	EI5
8	13,2	0	EI5
9	13,2	3	SI5
10	13,2	6	GI5
11	2,7	0	EI4
12	0	0	EI4
13	0	3	SI4
14	0	6	GI4
15	0	14,25	INV+
16	0	22,5	GI1
17	0	25,5	SI1
18	0	28,5	U
19	2,7	28,5	U
20	13,7	28,5	V
21	13,7	25,5	SI2
22	13,7	22,5	GI2
23	16,4	28,5	V
24	27,4	28,5	W
25	27,4	25,5	SI3
26	27,4	22,5	GI3
27	30,1	28,5	W
28	41,25	19,25	BRC+
29	49,5	28,5	NTC1
30	52,5	28,5	NTC2
31	52,5	16,95	INV+
32	52,5	14,25	INV+



Tolerance of pinpositions: ±0,5mm at the end of pins
Dimension of coordinate axis is only offset without tolerance

Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
TI4, TI1, TI5, TI2, TI6, TI3	IGBT	1200 V	25 A	Inverter Switch	
DI1, DI4, DI2, DI5, DI3, DI6	FWD	1200 V	25 A	Inverter Diode	
TB	IGBT	1200 V	25 A	Brake Switch	
DB2	FWD	1200 V	10 A	Brake Diode	
DB1	FWD	1200 V	3 A	Brake Sw. Protection Diode	
NTC	Thermistor			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 100	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* 1 packages see vincotech.com website.

Package data
Package data for *flow* 1 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
10-F1127PA025SC-L167E09-D5-14	5 May. 2022	New Datasheet format, module is unchanged	